



HIGH DENSITY MOUNTING HIGH VOLTAGE DARLINGTON OPTICALLY COUPLED ISOLATORS



APPROVALS

- UL recognised, File No. E91231

DESCRIPTION

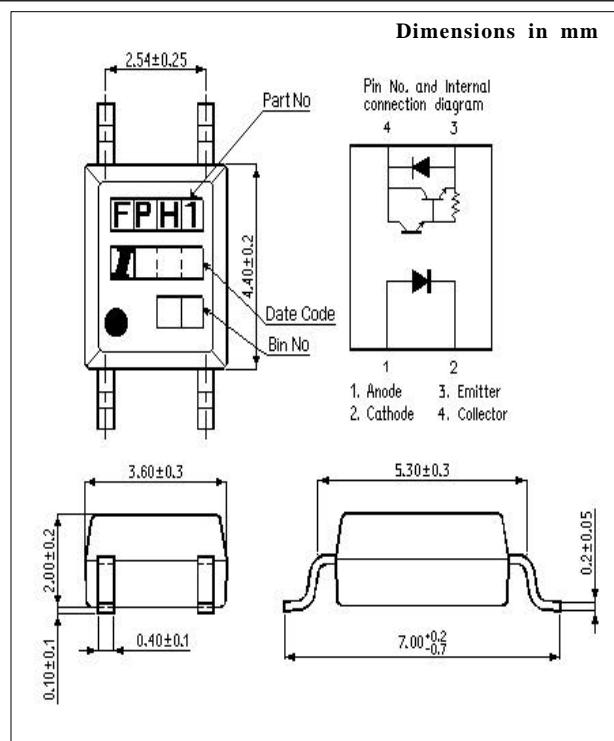
The IS452 is an optically coupled isolator consisting of an infrared light emitting diode and a high voltage NPN silicon photo darlington which has an integral base-emitter resistor to optimise switching speed and elevated temperature characteristics in a space efficient dual in line plastic package.

FEATURES

- Marked as FPH1.
- Current Transfer Ratio MIN. 1000%
- High collector-emitter voltage, $V_{CEO}=300V$
- Isolation Voltage ($3.75kV_{RMS}, 5.3kV_{PK}$)
- All electrical parameters 100% tested
- Drop in replacement for Sharp PC452

APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances



ABSOLUTEMAXIMUMRATINGS
(25°C unless otherwise specified)

Storage Temperature	-55°C to +150°C
Operating Temperature	-55°C to +100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUTDIODE

Forward Current	50mA
Reverse Voltage	6V
Power Dissipation	70mW

OUTPUTTRANSISTOR

Collector-emitter Voltage BV _{CEO}	300V
Emitter-collector Voltage BV _{ECO}	0.1V
Collector Current	150mA
Power Dissipation	150mW

POWERDISSIPATION

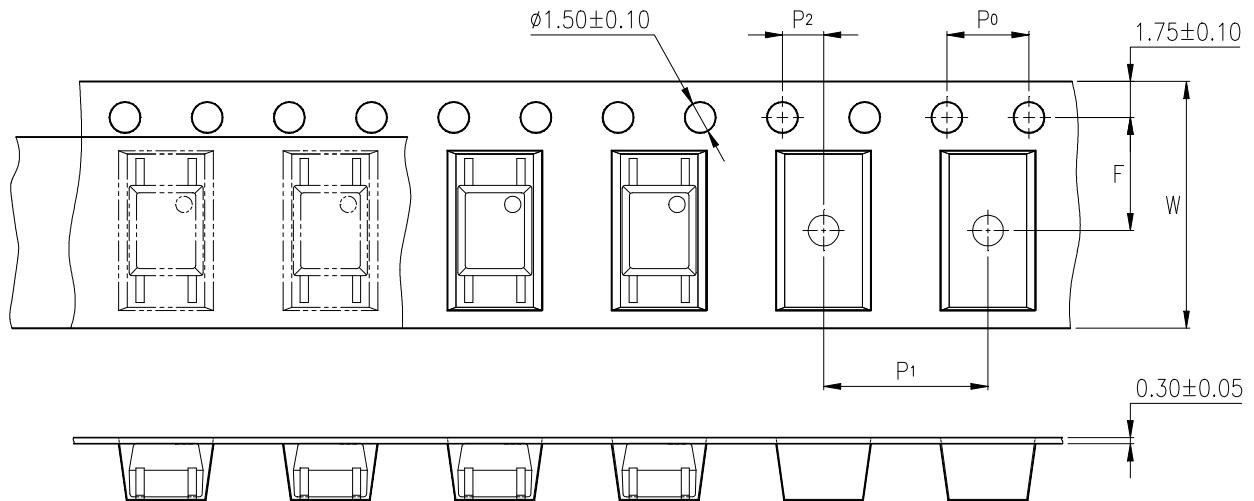
Total Power Dissipation	170mW
(derate linearly 2.26mW/°C above 25°C)	

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V _F)		1.2	1.4	V	I _F =10mA
	Reverse Current (I _R)			10	µA	V _R =4V
Output	Collector-emitter Breakdown (BV _{CEO})	300			V	I _C =0.1mA
	Emitter-collector Breakdown (BV _{ECO})	0.1			V	I _E = 10uA
	Collector-emitter Dark Current (I _{CEO})			200	nA	V _{CE} =200V
Coupled	Current Transfer Ratio (CTR)	1000			%	1mA I _F , 2V V _{CE}
	Collector-emitter Saturation Voltage V _{CE(SAT)}			1.2	V	20mA I _F , 100mA I _C
	Input to Output Isolation Voltage V _{ISO}	3750 5300			V _{RMS} V _{PK}	See note 1 See note 1
	Input-output Isolation Resistance R _{ISO}	5x10 ¹⁰			Ω	V _{IO} =500V (note 1)
	Output Rise Time tr Output Fall Time tf		4 3	18 18	µs µs	V _{CE} =2V, I _C =2mA, R _L =100Ω

Note 1 Measured with input leads shorted together and output leads shorted together.

TAPING DIMENSIONS



Description	Symbol	Dimensions in mm (inches)
Tape wide	W	12 ± 0.3 (.47)
Pitch of sprocket holes	P ₀	4 ± 0.1 (.15)
Distance of compartment	F	5.5 ± 0.1 (.217)
Distance of compartment to compartment	P ₂	2 ± 0.1 (.079)
Distance of compartment to compartment	P ₁	8 ± 0.1 (.315)

CHARACTERISTIC CURVES

Fig.1 Forward Current vs.
Ambient Temperature

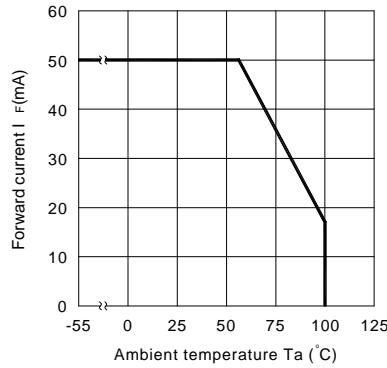


Fig.2 Collector Power Dissipation vs.
Ambient Temperature

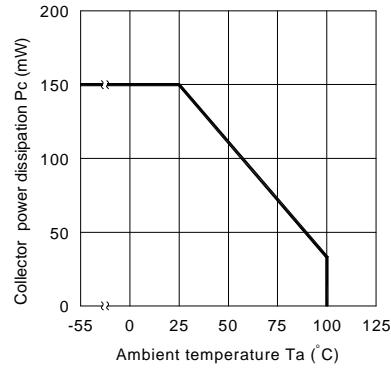


Fig.3 Collector-emitter saturation
Voltage vs. Forward current

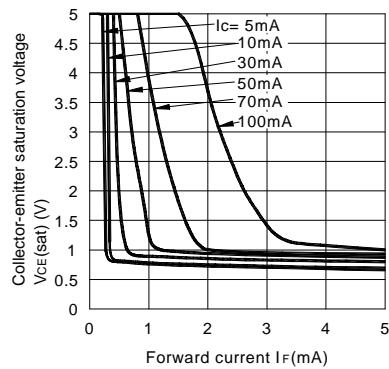


Fig.4 Forward Current vs. Forward
Voltage

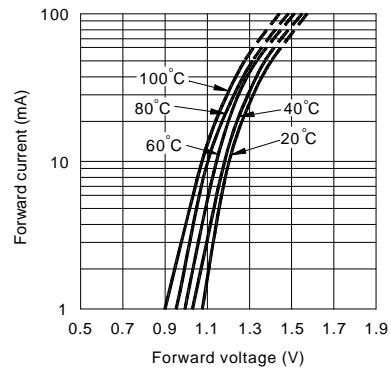


Fig.5 Current Transfer Ratio vs. Forward
Current

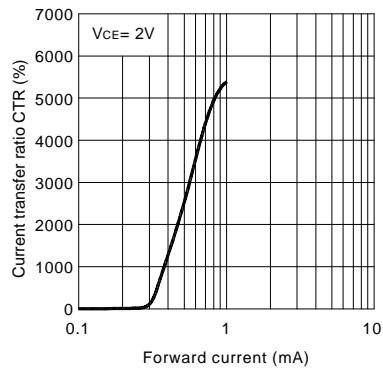
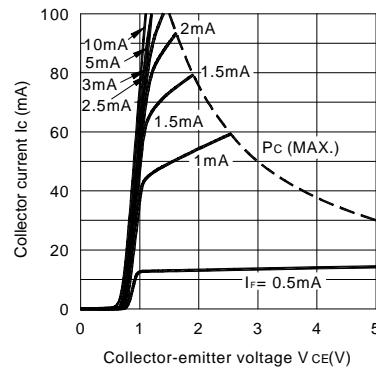


Fig.6 Collector Current vs.
Collector-emitter Voltage



CHARACTERISTIC CURVES

Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

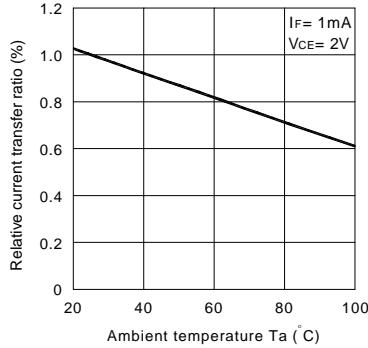


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

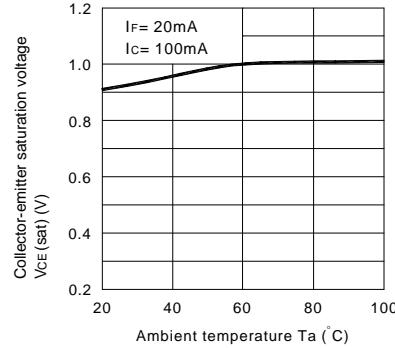


Fig.9 Collector Dark Current vs. Temperature

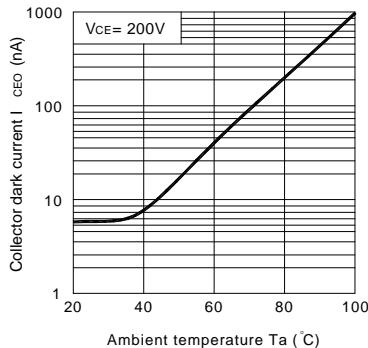


Fig.10 Response Time vs. Load Resistance

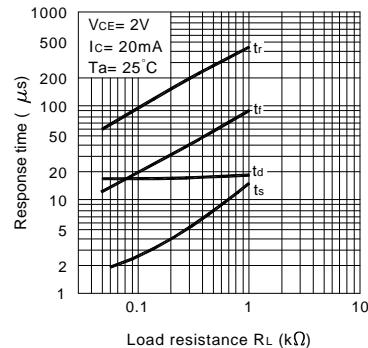
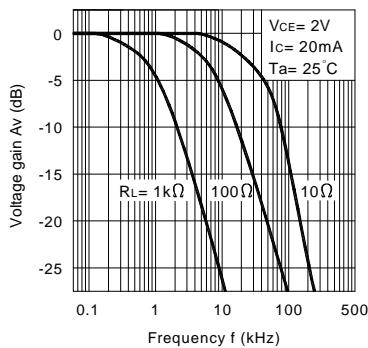
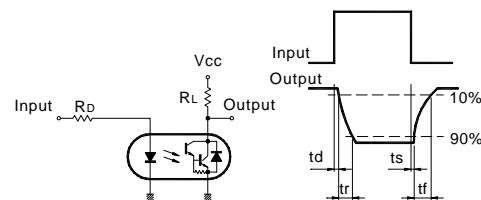


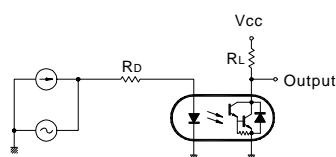
Fig.11 Frequency Response



Test Circuit for Response Time

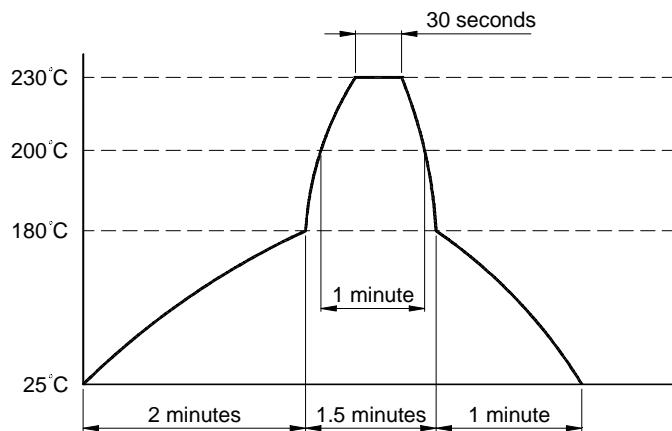


Test Circuit for Frequency Response



TEMPERATURE PROFILE OF SOLDERING REFLOW

- (1) One time soldering reflow is recommended within the condition of temperature and time profile shown below.



- (2) When using another soldering method such as infrared ray lamp, the temperature may rise partially in the mold of the device.
Keep the temperature on the package of the device within the condition of above (1).